

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	0	(external adj terminal) same (reference adj terminal ground GRND) same substrate same current same path same parallel same resistor same (coupled connected coupling connecting connection connexion) and (2nd second) and (3rd third).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 14:13
L4	152	(257/174).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2012/10/17 14:20
L5	86	4 and @ad<"20000208"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 14:23
S1	5	"498677".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:40
S2	32	(bidirectional bi-directional two-way comprehensive unified) near3 (electrostatic adj discharge esd).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 14:56
S3	30	steinhoff.in. and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:08
S4	2190	(esd electrostatic adj discharge).ti,ab,clm. and transistor and terminal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:09
S5	166	(esd electrostatic adj discharge).ti,ab,clm. and transistor and terminal and (bidirectional bi- directional "two way"\$1 comprehensive unified)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:10
S6	53	(esd electrostatic adj discharge).ti,ab,clm. and transistor and terminal and (bidirectional bi-	US-PGPUB; USPAT; EPO; JPO;	OR	ON	2006/06/10 15:22

		directional "two way"\$1 comprehensive unified) and @ad<"19991111"	DERWENT; IBM_TDB			
S7	218	common near4 "source/drain" and gate near4 connect\$3 near4 source and gate near4 connect\$3 near4 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25
S8	126	common near4 "source/drain" and gate near4 connect\$3 near4 source and gate near4 connect\$3 near4 drain and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25
S9	2408	257/355	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S10	1058	257/356	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S11	1139364	"57"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S12	7749759	"8"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S13	1179	257/360	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S14	3567	((257/173) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:27
S15	16	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter inverter))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:28
S16	17	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter inverter))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:58
S17	1822	(257/355).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:58
S18	207	S17 and inverter	US-PGPUB; USPAT;	OR	OFF	2006/09/19 16:00

			EPO; JPO; DERWENT; IBM_TDB			
S19	103	S17 and inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:13
S20	365	esd adj protection adj circuit and integrated adj circuit and (CMOS CMOSFET invert?) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:14
S21	454	esd adj protection adj circuit and integrated adj circuit and (BiCMOS CMOS CMOSFET invert?) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:08
S22	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:13
S23	4	"407037".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:14
S24	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S25	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S26	2	("6577481").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:17
S27	0	("690006.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18
S28	0	("690011.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18
S29	0	("6692606.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:19
S30	2	("6949800").PN.	US-PGPUB; USPAT;	OR	OFF	2006/09/19 17:19

			EPO; JPO; DERWENT; IBM_TDB				
S31	2	("6933741").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:20	
S32	2	("7060538").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:21	
S33	16	S22 S23 S24 S25 S26 S27 S28 S29 S30 S31 S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:23	
S34	6	(US-7060538-\$ or US-6949800-\$ or US-6919603-\$ or US-6784496-\$ or US-6577481-\$).did. or (US-6784496-\$).did.	USPAT; DERWENT	OR	OFF	2006/09/19 17:25	
S35	13	(bidirectional bi-directional) and ESD and biCMOS and SCR	USPAT; DERWENT	OR	ON	2006/09/19 17:53	
S36	16	(bidirectional bi-directional) and ESD and biCMOS and SCR	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:56	
S37	326	(257/358).COLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:23	
S38	1	"6369427".pn. and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29	
S39	190	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29	
S40	198	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:29	
S41	123	esd adj protection and cmos adj inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:30	
S42	2	"6369427".pn. and (ground terminal reference)	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	OFF	2006/09/20 08:57	

			IBM_TDB			
S43	1	"6369427".pn. and (substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 09:04
S44	1	esd and inverter and (duf buried) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S45	0	esd and inverter and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S46	0	esd and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S47	0	esd and (duf) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S48	236	esd and (buried adj (layer region)) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:35
S49	100	esd and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
S50	58	esd.ti,ab,clm. and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
S51	7	"498677".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 10:55
S52	2	"6369427".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 13:22
S53	1636	ra adj value	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 11:15
S54	3	ra adj value.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2007/06/05 11:15

			IBM_TDB			
S55	4	"185411".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/05 13:23
S56	2	("5,976,921").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:55
S57	3823	((257/173) or (257/174) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).OCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:56
S58	219	S57 and (esd electrostatic adj discharge) and (bi\$1directional\$2 symmetric\$2 symmetry reversible)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:01
S59	13	S57 and (esd electrostatic adj discharge) and (bi\$1directional\$2 symmetric\$2 symmetry reversible) and @ad<"19991111" and bias near4 (body substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:03
S60	16	((texas adj instrument\$1).as. (robert near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi\$1directional\$2 symmetric\$2 symmetry reversible) and @ad<"19991111" and bias near4 (body substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:07
S61	6	((texas adj instrument\$1).as. (robert near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi\$1directional\$2 symmetric\$2 symmetry reversible) and bias near4 (body substrate) and (bond adj pad external adj terminal).clm. and (transistor MOS MOSFET MI SFET MIS).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:39
S62	2	"6784496".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:14
S63	2	"6577481".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:15
S64	2	"6624481".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:15
S65	2	"6919603".pn.	US-PGPUB;	OR	ON	2007/06/06

			USPAT; EPO; JPO; DERWENT; IBM_TDB			11:16
S66	2	"6940131".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:19
S67	5	"926916".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:21
S68	4	"690006".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:22
S69	4	"690011".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:23
S70	3	("9949800").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:24
S71	2	("6949800").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:24
S72	2	("6933741").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:25
S73	2	("7060538").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:25
S74	2	("7034364").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
S75	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
S76	2	("6577481").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
S77	2	("6919603").PN.	US-PGPUB;	OR	OFF	2007/06/06

			USPAT; EPO; JPO; DERWENT; IBM_TDB			11:30
S78	2	("6940131").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:31
S79	2	("6424013").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:33
S80	2	("6628493").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:34
S81	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:35
S82	2	("6873506").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:36
S83	2	("5850095").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:36
S84	2	("5808342").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:37
S85	2	("5747834").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
S86	2	("6016002").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
S87	2	("6174404").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
S88	2	("6172404").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
S89	2	((texas adj instrument\$1).as. (robert	US-PGPUB;	OR	ON	2007/06/06

		near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi\$1directional\$2 symmetric\$2 symmetry reversible) and (third adj (transistor mosfet mos misfet)).clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB			11:40
S90	5080	((257/173) or (257/174) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).OCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2012/10/13 14:57
S91	524	H01L029/747.ipc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 14:57
S92	14	S91 and S90	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 14:58
S93	5590	S90 S91	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 15:11
S94	965	S93 and (third three "3") near2 (transistor MOS MOSFET BiCMOS CMOS CMOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 15:12
S95	142	S93 and (third three "3") near2 (transistor MOS MOSFET BiCMOS CMOS CMOSFET) and (resistance resistor) and parallel and @ad< "20000208"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 15:13
S96	0	(external adj terminal) same (reference adj terminal ground GRND) same (MOSFET transistor) same substrate same current same path same parallel same resistor same (coupled connected coupling connecting connection connexion) and second and third.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/13 15:24
S97	28	("7566595" or ("8110462") or ("7639463") or ("7427787") or ("7060538") or ("6933741") or ("7034364") or ("6949800") or ("7245466") or ("6940131") or ("6919603") or ("6624481") or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT;	OR	OFF	2012/10/13 15:30

		("6577481") or ("6784496").PN.	IBM_TDB			
S99	5081	((257/173) or (257/174) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2012/10/17 12:13
S100	524	H01L029/747.ipc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:14
S101	5591	S99 S100	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:14
S102	130	S101 and (third three "3" 3rd) near3 transistor and parallel and resistor near3 (second "2" 2nd)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:17
S103	285	(257/175).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2012/10/17 12:20
S104	0	S103 and @ad<"2000208"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:21
S105	193	S103 and @ad<"20000208"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:21
S106	1	S105 and (third three "3" 3rd) near3 transistor and parallel and resistor near3 (second "2" 2nd)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/10/17 12:28

10/17/2012 2:25:48 PM

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